REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED

REV																			
SHEET																			
REV																			
SHEET	15	16	17	18															

REV STATUS OF SHEETS	REV														
	SHEET	1	2	3	4	5	6	7	8	9	10	11	12	13	14

PMIC N/A

STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

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DRAWING APPROVAL DATE
96-03-22

REVISION LEVEL

DEFENSE ELECTRONICS SUPPLY CENTER
DAYTON, OHIO 45444

MICROCIRCUIT, DIGITAL, FAST CMOS, 8-BIT DIAGNOSTIC SCAN REGISTER, TTL COMPATIBLE INPUTS AND LIMITED OUTPUT VOLTAGE SWING, MONOLITHIC SILICON

SIZE	CAGE CODE	
A	67268	5962-96827

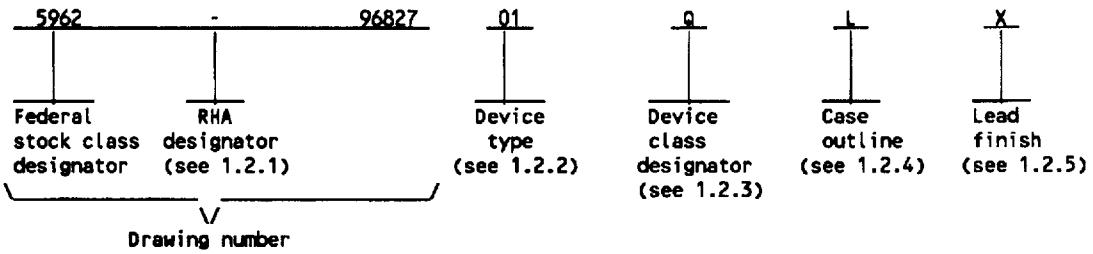
SHEET 1 OF 18

DESC FORM 193
JUL 94

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	29FCT818AT	8-bit diagnostic scan register, TTL compatible inputs and limited output voltage swing

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
L	GDIP3-T24 or CDIP4-T24	24	Dual-in-line
3	CQCC1-N28	28	Leadless chip carrier

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/ 2/ 3/

Supply voltage range (V_{CC})	-0.5 V dc to +7.0 V dc
DC input voltage range (V_{IN})	-0.5 V dc to V_{CC} + 0.5 V dc 4/
DC output voltage range (V_{OUT})	-0.5 V dc to V_{CC} + 0.5 V dc 4/
DC input clamp current (I_{IK}) (V_{IN} = -0.5 V)	-20 mA
DC output clamp current (I_{OK}) (V_{OUT} = -0.5 V and +7.0 V)	±20 mA
DC output source current (I_{OH}) (per output)	-30 mA
DC output sink current (I_{OL}) (per output)	+70 mA
DC V_{CC} current (I_{CC})	±268 mA
Ground current (I_{GND})	+588 mA
Storage temperature range (T_{STG})	-65°C to +150°C
Case temperature under bias (T_{BIAS})	-65°C to +135°C
Lead temperature (soldering, 10 seconds)	+300°C
Thermal resistance, junction-to-case (Θ_{JC})	See MIL-STD-1835
Junction temperature (T_J)	+175°C
Maximum power dissipation (P_D)	500 mW

1.4 Recommended operating conditions. 2/ 3/

Supply voltage range (V_{CC})	+4.5 V dc to +5.5 V dc
Input voltage range (V_{IN})	+0.0 V dc to V_{CC}
Output voltage range (V_{OUT})	+0.0 V dc to V_{CC}
Maximum low level input voltage (V_{IL})	0.8 V
Minimum high level input voltage (V_{IH})	2.0 V
Case operating temperature range (T_C)	-55°C to +125°C
Maximum input rise or fall rate ($\Delta t/\Delta V$):	
(from V_{IN} = 0.3 V to 2.7 V, 2.7 V to 0.3 V)	5 ns/V
Maximum high level output current (I_{OH})	-3 mA
Maximum low level output current (I_{OL})	20 mA

1.5 Digital logic testing for device classes Q and V.

Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012)	XX percent 5/

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solitation.

SPECIFICATION

MILITARY

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

2/ Unless otherwise noted, all voltages are referenced to GND.

3/ The limits for the parameters specified herein shall apply over the full specified V_{CC} range and case temperature range of -55°C to +125°C.

4/ For V_{CC} ≥ 6.5 V, the upper limit on the range is limited to 7.0 V.

5/ Values will be added when they become available.

STANDARDS

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.
MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines.

HANDBOOKS

MILITARY

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, bulletin, and handbook are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outlines. The case outlines shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Truth table. The truth table shall be as specified on figure 2.

3.2.4 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.5 Ground bounce load circuit and waveforms. The ground bounce load circuit and waveforms shall be as specified on figure 4.

3.2.6 Switching waveforms and test circuit. The switching waveforms and test circuit shall be as specified on figure 5.

3.2.7 Radiation exposure circuit. The radiation exposure circuit shall be as specified when available.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change for device class M. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 40 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table II herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.3.1 Electrostatic discharge sensitivity qualification inspection. Electrostatic discharge sensitivity (ESDS) testing shall be performed in accordance with MIL-STD-883, method 3015. ESDS testing shall be measured only for initial qualification and after process or design changes which may affect ESDS classification.

TABLE I. Electrical performance characteristics.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type	V_{CC}	Group A subgroups	Limits 3/		Unit
							Min	Max	
High level output voltage 3006	V_{OH1} 4/	For all inputs affecting output under test V_{IN} = 2.0 V or 0.8 V For all other inputs $V_{IN} = V_{CC}$ or GND	I_{OH} = -300 µA	All	4.5 V	1, 2, 3	3.0	V_{CC}-0.5	V
	V_{OH2}		I_{OH} = -3 mA			1, 2, 3	2.4		
Low level output voltage 3007	V_{OL1} 4/	For all inputs affecting output under test V_{IN} = 2.0 V or 0.8 V For all other inputs $V_{IN} = V_{CC}$ or GND	I_{OL} = 300 µA	All	4.5 V	1, 2, 3		0.2	V
	V_{OL2}		I_{OL} = 20 mA			1, 2, 3		0.55	
Negative input clamp voltage 3022	V_{IC-}	For input under test, I_{IN} = -18 mA		All	4.5 V	1, 2, 3		-1.2	V
Three-state output leakage current high 3021	I_{OZH} 5/ 6/	$\overline{OEY}$ = 2.0 V or 0.8 V For all other inputs $V_{IN} = V_{CC}$ or GND	V_{OUT} = 2.7 V	All	5.5 V	1, 2, 3		10.0	µA
Three-state output leakage current low 3020	I_{OZL} 5/ 6/		V_{OUT} = 0.5 V	All	5.5 V	1, 2, 3		-10.0	µA
Input current high 3010	I_{IH1}	For input under test, $V_{IN} = V_{CC}$ For all other inputs $V_{IN} = V_{CC}$ or GND		All	5.5 V	1, 2, 3		5.0	µA
Input current high 3010	I_{IH2}	For input under test, V_{IN} = 2.7 V For all other inputs $V_{IN} = V_{CC}$ or GND		All	5.5 V	1, 2, 3		±1.0	µA
Input current low 3009	I_{IL}	For input under test, V_{IN} = 0.5 V For all other inputs $V_{IN} = V_{CC}$ or GND		All	5.5 V	1, 2, 3		±1.0	µA
Power-off leakage current	I_{OFF}	V_{OUT} = 4.5 V		All	0.0 V	1, 2, 3		±1.0	µA
Output short circuit current 3011	I_{OS} 7/	For all inputs V_{IN} = 2.0 V or 0.8 V V_{OUT} = 0.0 V		All	5.5 V	1, 2, 3	-60	-225	mA
Dynamic power supply current	I_{CCD} 4/ 8/	Outputs open		All	5.5 V	4, 5, 6		250	µA/ MHz•Bit
Quiescent supply current delta, TTL input level 3005	ΔI_{CC} 9/	For input under test V_{IN} = 3.4 V For all other inputs $V_{IN} = V_{CC}$ or GND		All	5.5 V	1, 2, 3		2.0	mA

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified		Device type	V_{CC}	Group A subgroups	Limits 3/		Unit
							Min	Max	
Quiescent supply current, outputs high 3005	I_{CCH}	$\overline{OEY}$ = GND For all other inputs $V_{IN} = V_{CC}$ or GND		All	5.5 V	1, 2, 3		1.5	mA
Quiescent supply current, outputs low 3005	I_{CCL}			All	5.5 V	1, 2, 3		1.5	mA
Quiescent supply current, outputs disabled 3005	I_{CCZ} 5/	$\overline{OEY} = V_{CC}$ For all other inputs $V_{IN} = V_{CC}$ or GND		All	5.5 V	1, 2, 3		1.5	mA
Total supply current	I_{CCT1} 10/	Outputs open f_{CP} = 10 MHz $\overline{OEY}$ = GND One bit toggling f_i = 5 MHz 50% duty cycle For nonswitching input, $V_{IN} = V_{CC}$ or GND	For switching inputs $V_{IN} = V_{CC}$ or GND	All	5.5 V	4, 5, 6		5.3	mA
			For switching inputs V_{IN} = 3.4 V or GND			4, 5, 6		7.3	
	I_{CCT2} 4/ 10/	Outputs open f_{CP} = 10 MHz $\overline{OEY}$ = GND Eight bits and four controls toggling f_i = 5 MHz 50% duty cycle For nonswitching input, $V_{IN} = V_{CC}$ or GND	For switching inputs $V_{IN} = V_{CC}$ or GND	All	5.5 V	4, 5, 6		17.8	
			For switching inputs V_{IN} = 3.4 V or GND			4, 5, 6		30.8	
Input capacitance 3012	C_{IN} 11/	T_C = +25°C See 4.4.1b		All	GND	4		10.0	pF
Output capacitance 3012	C_{OUT} 11/			All	GND	4		12.0	pF
Low level ground bounce noise	V_{OLP} 11/ 12/	V_{IH} = 3.0 V, V_{IL} = 0.0 V T_A = +25°C See 4.4.1d See figure 4		All	5.0 V	4		1750	mV
	V_{OLV} 11/ 12/					4		-1100	
High level V_{CC} bounce noise	V_{OHP} 11/ 12/			All	5.0 V	4		800	mV
	V_{OHV} 11/ 12/					4		-1200	
Functional test 3014	13/	V_{IH} = 2.0 V, V_{IL} = 0.8 V Verify output V_O See 4.4.1c		All	4.5 V	7, 8	L	H	
					5.5 V	7, 8	L	H	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified	Device type	V_{CC}	Group A subgroups	Limits 3/		Unit
						Min	Max	
Propagation delay time, PCLK to Y_n 3003	t_{PLH1}, t_{PHL1} 14/	C_L = 50 pF minimum R_L = 500Ω See figure 5	All	4.5 V	9, 10, 11	2.0	12.0	ns
Propagation delay time, MODE to SDO 3003	t_{PLH2}, t_{PHL2} 14/		All	4.5 V	9, 10, 11	2.0	18.0	ns
Propagation delay time, SDI to SDO 3003	t_{PLH3}, t_{PHL3} 14/		All	4.5 V	9, 10, 11	2.0	18.0	ns
Propagation delay time, DCLK to SDO 3003	t_{PLH4}, t_{PHL4} 14/		All	4.5 V	9, 10, 11	2.0	30.0	ns
Propagation delay time, output enable, $\overline{OEY}$ to Y_n 3003	t_{PZH1} 14/		All	4.5 V	9, 10, 11	3.0	20.0	ns
	t_{PZL1} 14/				9, 10, 11	3.0	20.0	
Propagation delay time, output enable, DCLK to D_n 3003	t_{PZH2} 14/		All	4.5 V	9, 10, 11	3.0	30.0	ns
	t_{PZL2} 14/				9, 10, 11	3.0	35.0	
Propagation delay time, output disable, $\overline{OEY}$ to Y_n 3003	t_{PHZ1} 14/		All	4.5 V	9, 10, 11	3.0	30.0	ns
	t_{PLZ1} 14/				9, 10, 11	3.0	20.0	
Propagation delay time, output disable, DCLK to D_n 3003	t_{PHZ2} 14/		All	4.5 V	9, 10, 11	3.0	90.0	ns
	t_{PLZ2} 14/				9, 10, 11	3.0	45.0	
Setup time, high or low, D_n to PCLK	t_{s1} 14/		All	4.5 V	9, 10, 11	6.0		ns
Setup time, high or low, MODE to PCLK	t_{s2} 14/		All	4.5 V	9, 10, 11	15.0		ns
Setup time, high or low, Y_n to DCLK	t_{s3} 14/		All	4.5 V	9, 10, 11	5.0		ns
Setup time, high or low, MODE to DCLK	t_{s4} 14/		All	4.5 V	9, 10, 11	12.0		ns
Setup time, high or low, SDI to DCLK	t_{s5} 14/		All	4.5 V	9, 10, 11	10.0		ns

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test and MIL-STD-883 test method 1/	Symbol	Test conditions 2/ $-55°C \le T_C \le +125°C$ $+4.5\ V \le V_{CC} \le +5.5\ V$ unless otherwise specified	Device type	V_{CC}	Group A subgroups	Limits 3/		Unit
						Min	Max	
Setup time, high or low, DCLK to PCLK	t_{s6} 14/	C_L = 50 pF minimum R_L = 500Ω See figure 5	All	4.5 V	9, 10, 11	15.0		ns
Setup time, high or low, PCLK to DCLK	t_{s7} 14/		All	4.5 V	9, 10, 11	45.0		ns
Hold time, high or low, D_n to PCLK	t_{h1} 14/		All	4.5 V	9, 10, 11	2.0		ns
Hold time, high or low, MODE to PCLK	t_{h2} 14/		All	4.5 V	9, 10, 11	0.0		ns
Hold time, high or low, Y_n to DCLK	t_{h3} 14/		All	4.5 V	9, 10, 11	5.0		ns
Hold time, high or low, MODE to DCLK	t_{h4} 14/		All	4.5 V	9, 10, 11	5.0		ns
Hold time, high or low, SDI to DCLK	t_{h5} 14/		All	4.5 V	9, 10, 11	0.0		ns
PCLK pulse width, high or low	t_{w1} 14/		All	4.5 V	9, 10, 11	15.0		ns
DCLK pulse width, high or low	t_{w2} 14/		All	4.5 V	9, 10, 11	25.0		ns

1/ For tests not listed in the referenced MIL-STD-883 (e.g. ΔI_{CC}), utilize the general test procedure of 883 under the conditions listed herein.

2/ Each input/output, as applicable, shall be tested at the specified temperature, for the specified limits, to the tests in table I herein. Output terminals not designated shall be high level logic, low level logic, or open, except for all I_{CC} and ΔI_{CC} tests, the output terminals shall be open. When performing these tests, the current meter shall be placed in the circuit such that all current flows through the meter.

3/ For negative and positive voltage and current values, the sign designates the potential difference in reference to GND and the direction of current flow, respectively; and the absolute value of the magnitude, not the sign, is relative to the minimum and maximum limits, as applicable, listed herein. All devices shall meet or exceed the limits specified in table I at $4.5\ V \le V_{CC} \le 5.5\ V$.

4/ This parameter is guaranteed, if not tested, to the limits specified in table I herein.

5/ Three-state output conditions are required.

6/ This test may be performed using V_{IH} = 3.0 V. When V_{IH} = 3.0 V is used, the test is guaranteed for V_{IH} = 2.0 V.

7/ Not more than one output should be tested at a time. The duration of the test should not exceed one second.

8/ I_{CCD} may be verified by the following equation:

$$I_{CCD} = \frac{I_{CCT} - I_{CC} - D_H N_T \Delta I_{CC}}{f_{CP}/2 + f_i N_i}$$

where I_{CCT}, I_{CC} (I_{CCL} or I_{CCH} in table I), and ΔI_{CC} shall be the measured values of these parameters, for the device under test, when tested as described in table I, herein. The values for D_H, N_T, f_{CP}, f_i, and N_i shall be as listed in the test conditions column for I_{CCT} in table I, herein.

TABLE I. Electrical performance characteristics - Continued.

9/ This test may be performed either one input at a time (preferred method) or with all input pins simultaneously at $V_{IN} = V_{CC} - 2.1$ V (alternate method). Classes Q and V shall use the preferred method. When the test is performed using the alternate test method, the maximum limit is equal to the number of inputs at a high TTL input level times 2.0 mA; and the preferred method and limits are guaranteed.

10/ I_{CCT} is calculated as follows:

$$I_{CCT} = I_{CC} + D_H N_T \Delta I_{CC} + I_{CCD}(f_{CP}/2 + f_i N_i)$$

where
I_{CC} = Quiescent supply current (any I_{CCL} or I_{CCH})
D_H = Duty cycle for TTL inputs at 3.4 V
N_T = Number of TTL inputs at 3.4 V
ΔI_{CC} = Quiescent supply current delta, TTL inputs at 3.4 V
I_{CCD} = Dynamic power supply current caused by an input transition pair (HLH or LHL)
f_{CP} = Clock frequency for registered devices (f_{CP} = 0 for nonregistered devices)
f_i = Input frequency
N_i = Number of inputs at f_i

11/ This test is required only for group A testing; see 4.4.1 herein.

12/ This test is for qualification only. Ground and V_{CC} bounce tests are performed on a non-switching (quiescent) output and are used to measure the magnitude of induced noise caused by other simultaneously switching outputs. The test is performed on a low noise bench test fixture. For the device under test, all outputs shall be loaded with 500Ω of load resistance and a minimum of 50 pF of load capacitance (see figure 4). Only chip capacitors and resistors shall be used. The output load components shall be located as close as possible to the device outputs. It is suggested, that whenever possible, this distance be kept to less than 0.25 inches. Decoupling capacitors shall be placed in parallel from V_{CC} to ground. The values of these decoupling capacitors shall be determined by the device manufacturer. The low and high level ground and V_{CC} bounce noise is measured at the quiet output using a 1 GHz minimum bandwidth oscilloscope with a 50Ω input impedance.

The device inputs shall be conditioned such that all outputs are at a high nominal V_{OH} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OH} as all other outputs possible are switched from V_{OH} to V_{OL}. V_{OHV} and V_{OHP} are then measured from the nominal V_{OH} level to the largest negative and positive peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OL} to V_{OH}.

The device inputs shall be conditioned such that all outputs are at a low nominal V_{OL} level. The device inputs shall then be conditioned such that they switch simultaneously and the output under test remains at V_{OL} as all other outputs possible are switched from V_{OL} to V_{OH}. V_{OLP} and V_{OLV} are then measured from the nominal V_{OL} level to the largest positive and negative peaks, respectively (see figure 4). This is then repeated with the same outputs not under test switching from V_{OH} to V_{OL}.

13/ Tests shall be performed in sequence, attributes data only. Functional tests shall include the truth table and other logic patterns used for fault detection. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. Functional tests shall be performed in sequence as approved by the qualifying activity on qualified devices. For outputs, L < 1.5 V, H ≥ 1.5 V.

14/ AC limits at V_{CC} = 5.5 V are equal to the limits at V_{CC} = 4.5 V and guaranteed by testing at V_{CC} = 4.5 V. Minimum propagation delay time limits for V_{CC} = 4.5 V and 5.5 V are guaranteed, if not tested, to the limits specified in table I, herein. For propagation delay tests, all paths must be tested.

Device type	All				
Case outlines	L	3	Case outlines	L	3
Terminal number	Terminal symbol	Terminal symbol	Terminal number	Terminal symbol	Terminal symbol
1	$\overline{OEY}$	NC	15	Y_7	NC
2	DCLK	$\overline{OEY}$	16	Y_6	PCLK
3	D_0	DCLK	17	Y_5	SDO
4	D_1	D_0	18	Y_4	Y_7
5	D_2	D_1	19	Y_3	Y_6
6	D_3	D_2	20	Y_2	Y_5
7	D_4	D_3	21	Y_1	Y_4
8	D_5	NC	22	Y_0	NC
9	D_6	D_4	23	MODE	Y_3
10	D_7	D_5	24	V_{CC}	Y_2
11	SDI	D_6	25	---	Y_1
12	GND	D_7	26	---	Y_0
13	PCLK	SDI	27	---	MODE
14	SDO	GND	28	---	V_{CC}

NC = No connection.

Terminal descriptions	
Terminal symbol	Description
D_n (n = 0 to 7)	Parallel data inputs to the pipeline register or parallel data outputs from the shadow register
DCLK	Diagnostics clock input for loading shadow register
PCLK	Pipeline register clock input loads D-port or shadow register contents on low-to-high transition
MODE	Control input for pipeline register multiplexer and shadow register control
$\overline{OEY}$	Output enable control input for Y-port (active low)
SDI	Serial data input to shadow register
SDO	Serial data output from shadow register
Y_n (n = 0 to 7)	Data outputs from the pipeline register or parallel inputs to the shadow register

FIGURE 1. Terminal connections.

Inputs				Outputs			Operation
MODE	SDI	DCLK	PCLK	SDO	Shadow register	Pipeline register	
L	X	↑	X	S_7	$S_0 \leftarrow SDI$ $Sn \leftarrow S_{n-1}$	NA	Serial shift; D_7-D_0 outputs disabled
L	X	X	↑	S_7	NA	$P_n \leftarrow D_n$	Load pipeline register from data inputs
H	L	↑	X	L	$S_n \leftarrow Y_n$	NA	Load shadow register from Y_n outputs
H	H	↑	X	H	Hold	NA	Hold shadow register; D_7-D_0 outputs enabled
H	X	X	↑	SDI	NA	$P_n \leftarrow S_n$	Load pipeline register from shadow register

H = High voltage level
L = Low voltage level
X = Irrelevant
↑ = Low-to-high clock transition
S_n (n = 7 to 0) = Shadow register outputs
P_n (n = 7 to 0) = Pipeline register outputs
NA = Not applicable; output is not a function of the specified input combinations

FIGURE 2. Truth table.

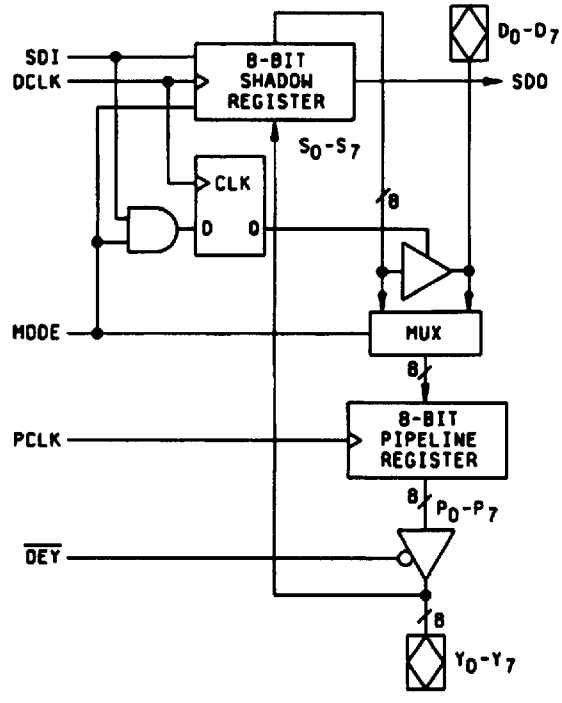


FIGURE 3. Logic diagram.

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		REVISION LEVEL	SHEET 12

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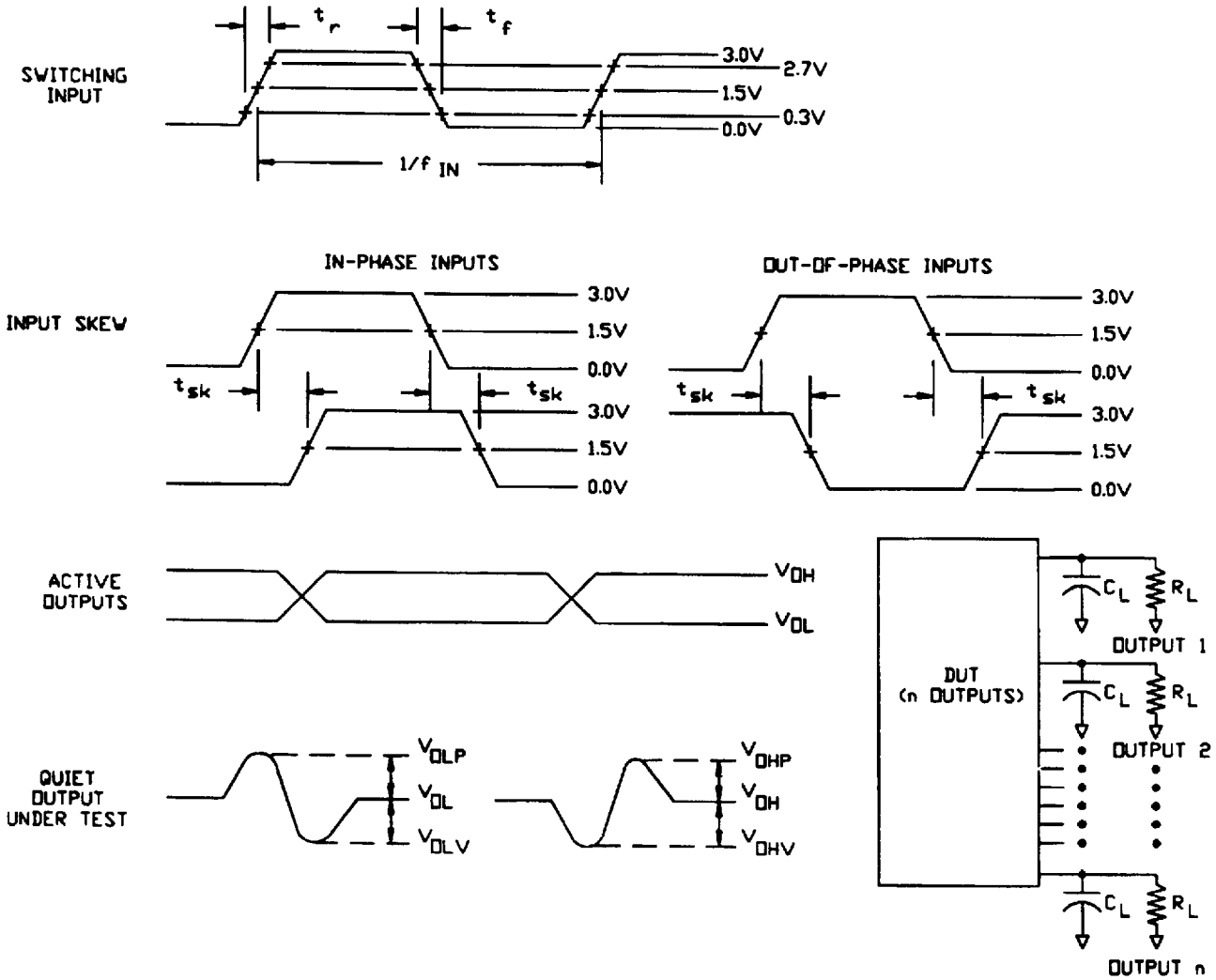


NOTES:

1. C_L includes a 47 pF chip capacitor (-0 percent, +20 percent) and at least 3 pF of equivalent capacitance from the test jig and probe.
2. R_L = 450Ω ±1 percent, chip resistor in series with a 50Ω termination. For monitored outputs, the 50Ω termination shall be the 50Ω characteristic impedance of the coaxial connector to the oscilloscope.
3. Input signal to the device under test:
   a. V_{IN} = 0.0 V to 3.0 V; duty cycle = 50 percent; $f_{IN} \geq 1$ MHz.
   b. t_r, t_f = 3 ns ±1.0 ns. For input signal generators incapable of maintaining these values of t_r and t_f, the 3.0 ns limit may be increased up to 10 ns, as needed, maintaining the ±1.0 ns tolerance and guaranteeing the results at 3.0 ns ±1.0 ns; skew between any two switching inputs signals (t_{sk}): ≤ 250 ps.

FIGURE 4. Ground bounce load circuit and waveforms.

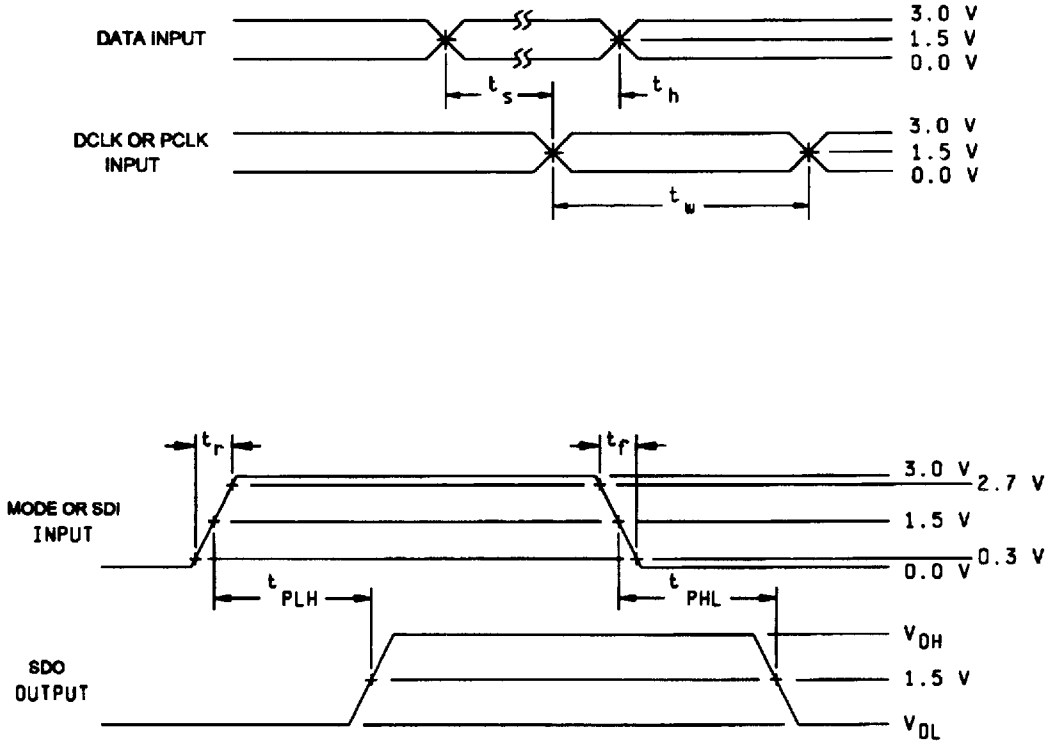
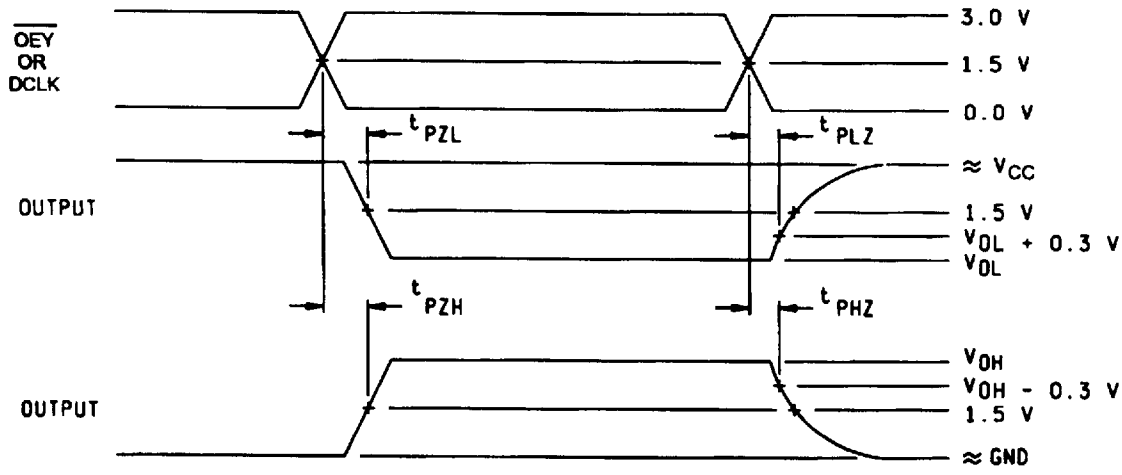
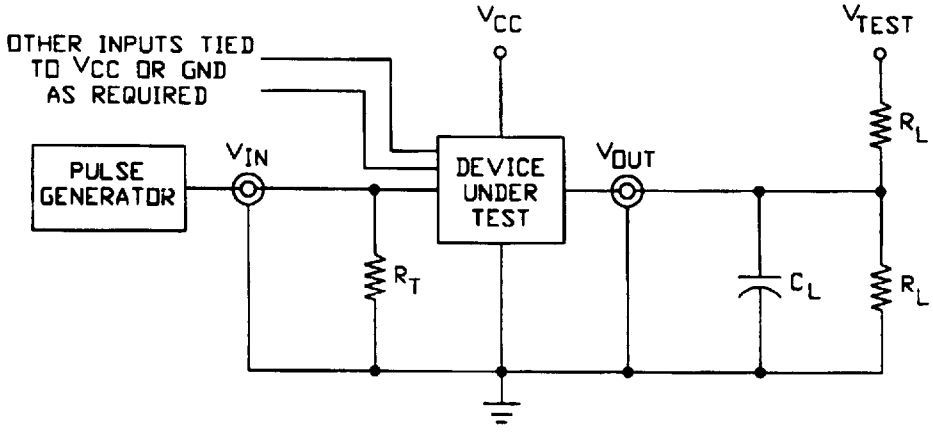


FIGURE 5. Switching waveforms and test circuit.





NOTES:
1. When measuring t_{PLZ} and t_{PZL}: V_{TEST} = 7.0 V.
2. When measuring t_{PHZ}, t_{PZH}, t_{PLH}, and t_{PHL}: V_{TEST} = open.
3. The t_{PZL} and t_{PLZ} reference waveform is for the output under test with internal conditions such that the output is at V_{OL} except when disabled by the output enable control. The t_{PZH} and t_{PHZ} reference waveform is for the output under test with internal conditions such that the output is at V_{OH} except when disabled by the output enable control.
4. C_L = 50 pF minimum or equivalent (includes test jig and probe capacitance).
5. R_L = 500Ω or equivalent.
6. R_T = 50Ω or equivalent.
7. Input signal from pulse generator: V_{IN} = 0.0 V to 3.0 V; PRR ≤ 10 MHz; t_r ≤ 2.5 ns; t_f ≤ 2.5 ns; t_r and t_f shall be measured from 0.3 V to 2.7 V and from 2.7 V to 0.3 V, respectively; duty cycle = 50 percent.
8. Timing parameters shall be tested at a minimum input frequency of 1 MHz.
9. The outputs are measured one at a time with one transition per measurement.

FIGURE 5. Switching waveforms and test circuit - Continued.

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. C_{IN} and C_{OUT} shall be measured only for initial qualification and after process or design changes which may affect capacitance. C_{IN} and C_{OUT} shall be measured between the designated terminal and GND at a frequency of 1 MHz. For C_{IN} and C_{OUT}, test all applicable pins on five devices with zero failures.

For C_{IN} and C_{OUT}, a device manufacturer may qualify devices by functional groups. A specific functional group shall be composed of function types, that by design, will yield the same capacitance values when tested in accordance with table I herein. The device manufacturer shall set a functional group limit for the C_{IN} and C_{OUT} tests. The device manufacturer may then test one device function from a functional group to the limits and conditions specified herein. All other device functions in that particular functional group shall be guaranteed, if not tested, to the limits and conditions specified in table I herein. The device manufacturer shall submit to DESC-EC the device functions listed in each functional group and the test results for each device tested.

c. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table in figure 2 herein. The test vectors used to verify the truth table shall, at a minimum, test all functions of each input and output. All possible input to output logic patterns per function shall be guaranteed, if not tested, to the truth table in figure 2 herein. For device classes Q and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).

d. Ground and V_{CC} bounce tests are required for all device classes. These tests shall be performed only for initial qualification, after process or design changes which may affect the performance of the device, and any changes to the test fixture. V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} shall be measured for the worst case outputs of the device. All other outputs shall be guaranteed, if not tested, to the limits established for the worst case outputs. The worst case outputs tested are to be determined by the manufacturer. Test 5 devices assembled in the worst case package type supplied to this document. All other package types shall be guaranteed, if not tested, to the limits established for the worst case package. The package type to be tested shall be determined by the manufacturer. The device manufacturer will submit to DESC-EC data that shall include all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

Each device manufacturer shall test product on the fixtures they currently use. When a new fixture is used, the device manufacturer shall inform DESC-EC of this change and test the 5 devices on both the new and old test fixtures. The device manufacturer shall then submit to DESC-EC data from testing on both fixtures that shall include all measured peak values for each device tested and detailed oscilloscope plots for each V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} from one sample part per function. The plot shall contain the waveforms of both a switching output and the output under test.

For V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV}, a device manufacturer may qualify devices by functional groups. A specific functional group shall be composed of function types, that by design, will yield the same test values when tested in accordance with table I herein. The device manufacturer shall set a functional group limit for the V_{OLP}, V_{OLV}, V_{OHP}, and V_{OHV} tests. The device manufacturer may then test one device function from a functional group to the limits and conditions specified herein. All other device functions in that particular functional group shall be guaranteed, if not tested, to the limits and conditions specified in table I herein. The device manufacturer shall submit to DESC-EC the device functions listed in each functional group and the test results, along with the oscilloscope plots, for each device tested.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	---	1	1
Final electrical parameters (see 4.2)	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 1/	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 1/	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11 2/
Group A test requirements (see 4.4)	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11	1, 2, 3, 4, 5, 6, 7, 8, 9, 10, 11
Group C end-point electrical parameters (see 4.4)	1, 2, 3, 4, 5, 6	1, 2, 3, 4, 5, 6	1, 2, 3, 4, 5, 6 7, 8, 9, 10, 11
Group D end-point electrical parameters (see 4.4)	1, 2, 3	1, 2, 3	1, 2, 3
Group E end-point electrical parameters (see 4.4)	1, 4, 7, 9	1, 4, 7, 9	1, 4, 7, 9

1/ PDA applies to subgroups 1 and 4 (i.e., I_{CCT} only).
2/ PDA applies to subgroups 1, 4, and 7.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. Test condition A, B, C, or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

b. T_A = +125°C, minimum.

c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

a. End-point electrical parameters shall be as specified in table II herein.

b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

4.5 Methods of inspection. Methods of inspection shall be specified as follows:

4.5.1 Voltage and current. Unless otherwise specified, all voltages given are referenced to the microcircuit GND terminal. Currents given are conventional current and positive when flowing into the referenced terminal.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.

6.4 Comments. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444-5270, or telephone (513) 296-5377.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.